Contents

1 Introduction to Quantum Dots ........................................... 1
  1.1 Physics of Zero-Dimensional Structures .......................... 1
  1.2 Electronic Properties of Quantum Dots ........................... 2
  1.3 Fabrication of Quantum Dots ........................................... 4
  1.4 Electronic Spectra of Self-assembled QDs ......................... 5
  1.5 Disadvantages of Self-assembled QDs ............................... 6
  1.6 Methods for Improving QD Characteristics ....................... 7
    1.6.1 Different In-Situ and Ex-Situ Techniques for Improving
         QD Characteristics ............................................. 7
    1.6.2 Importance of Capping Layers for Improving QD
         Characteristics ................................................... 8
  1.7 Summary ........................................................... 9
References ........................................................................ 10

2 Low-Energy Ion Implantation Over Single-Layer InAs/GaAs
  Quantum Dots ............................................................... 13
  2.1 Motivation Behind Ion Implantation Study ......................... 13
  2.2 Scope of the Present Study ............................................ 14
  2.3 Growth of Single-Layer InAs/GaAs QDs ............................. 15
  2.4 Ion Implantation and Post-Growth Experiments on QDs ............ 16
  2.5 Results and Discussion ................................................. 16
    2.5.1 Structural, Material and Optical Properties of S⁻
         Ion-Implanted InAs/GaAs QDs ................................. 16
    2.5.2 Structural, Material and Optical Properties of H⁻
         Ion-Implanted InAs/GaAs QDs ................................. 20
  2.6 Conclusions Obtained from the Results of Heavy and Light
         Ion Implantation on InAs/GaAs QDs ............................ 24
References ................................................................. 25
3 Optimizations for Quaternary Alloy (InAlGaAs)-Capped InAs/GaAs Multilayer Quantum Dots

3.1 Motivation Behind the Study .............................. 28
3.2 Importance of Multilayer QDs ............................. 28
3.3 Growth of Different Quaternary Alloy-Capped Multilayer InAs/GaAs QDs ........................................ 28
3.4 Post-Growth Experiments Performed on MQDs ................ 30
3.5 Results and Discussion .................................. 30
3.5.1 Effects of Variation in Growth Rate of QDs in InAs/GaAs MQD System ................................. 31
3.5.2 Impact of Variation in Quaternary Capping Thickness in InAs/GaAs MQD System ................................. 33
3.5.3 Effects of Variations in Seed QD Monolayer Coverage for Quaternary Alloy-Capped InAs/GaAs MQDs .......... 33
3.5.4 Effects of Rapid Thermal Annealing (Ex-Situ) on Quaternary Alloy-Capped InAs/GaAs MQDs ............. 34
3.6 Significant Results of Study of Quaternary Alloy-Capped InAs/GaAs MQDs ...................................... 38

References ................................................ 39

4 Effects of Low Energy Light Ion (H\(^{-}\)) Implantations on Quaternary-Alloy-Capped InAs/GaAs Quantum Dot Infrared Photodetectors ................................. 41

4.1 Introduction: Basic Operation of Intersubband Detectors ........ 41
4.2 Advantages of QDIPs ................................... 42
4.3 Previously Reported Results on In(Ga)As/GaAs QDIPs .......... 43
4.4 Growth of Quaternary Alloy-Capped InAs/GaAs QDIPs ........ 44
4.5 Optimization of H\(^{-}\) Ion Fluence and Implantation .......... 45
4.6 Fabrication of Mesa-Shaped Single-Pixel Devices on Implanted Samples .............................................. 46
4.7 Different Characterizations Performed for Implanted QDIPs .... 50
4.8 Results and Discussion .................................. 50
4.8.1 Optical and Structural Properties of H\(^{-}\) Ion-Implanted InAs/GaAs QDIPs ................................ 50
4.8.2 Electrical Properties of H\(^{-}\) Ion-Implanted InAs/GaAs QDIPs ........................................... 52
4.9 Significant Results from H\(^{-}\) Ion-Implanted InAs/GaAs QDIPs and Conclusions ............................... 55

References ................................................ 55

5 Effects of Low-Energy Light Ion (H\(^{-}\)) Implantation on Quaternary-Alloy-Capped InGaAs/GaAs Quantum Dot Infrared Photodetectors ................................. 57

5.1 Scope of the Study ..................................... 57
5.2 Growth of Quaternary-Alloy-Capped InGaAs/GaAs QDIPs .......... 58
5.3 Ion Implantation, Device Fabrication and Different Characterizations for $H^-$ Ion-Implanted InGaAs/GaAs QDIPs .................. 59
5.4 Results and Discussion .................................. 60
  5.4.1 Optical Properties of $H^-$ Ion-Implanted InGaAs/GaAs QDIPs ........................................ 60
  5.4.2 Electrical Properties of $H^-$ Ion-Implanted InGaAs/GaAs QDIPs ...................................... 60
5.5 Significant Results from $H^-$ Ion-Implanted InGaAs/GaAs QDIPs and Conclusions ......................... 63
References ............................................................................... 64
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